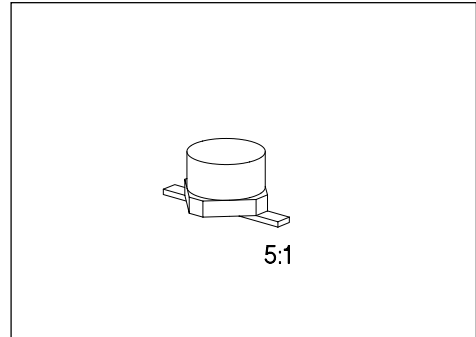


## Silicon Schottky Diode

**BAT 32**

- RF detector
- Low-power mixer
- Zero bias
- Very low capacitance
- For frequencies up to 18 GHz
- HiRel/Mil-tested diodes available



**ESD:** Electrostatic discharge sensitive device, observe handling precautions!

Type	Frequency band (GHz)	Marking	Ordering Code (tape and reel)	Pin Configuration	Package <sup>1)</sup>
BAT 32	... 18 (X, Ku)	32	Q62702-A826		Cerec-X

### Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	$V_R$	6.5	V
Forward current	$I_F$	50	mA
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	- 55 ... + 150	
Operating temperature range	$T_{op}$	- 55 ... + 150	

<sup>1)</sup> For detailed information see chapter Package Outlines.

## Electrical Characteristics

at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage $I_R = 1\text{ mA}$	$V_{(BR)}$	6.5	–	–	V
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$	$V_F$	– –	0.2 0.6	– –	
Diode capacitance $V_R = 0.15\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	–	0.20	0.24	pF
Differential resistance $V_F = 0$ , $f = 10\text{ kHz}$	$R_o$	–	15	–	k $\Omega$

## Forward current $I_F = f(V_F)$

